Octal Bus Buffer

The MC74VHC541 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC541 is a noninverting type. When either $\overline{OE1}$ or $\overline{OE2}$ are high, the terminal outputs are in the high impedance state.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 3.7 \text{ns}$ (Typ) at $V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A$ (Max) at $T_A = 25^{\circ}C$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2.0 V to 5.5 V Operating Range
- Low Noise: V_{OLP} = 1.2 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 134 FETs or 33.5 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

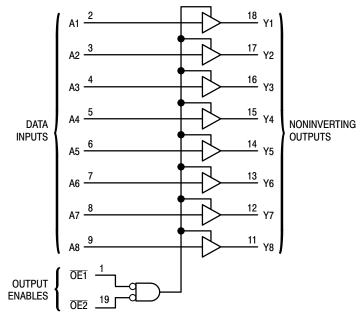


Figure 1. Logic Diagram



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SOIC-20WB SUFFIX DW CASE 751D



TSSOP-20 SUFFIX DT CASE 948E

PIN ASSIGNMENT

OE1	d	1 ●	20	v _{cc}
A 1	d :	2	19	OE2
A2	d :	3	18	Y1
А3	ф.	4	17] Y2
A4	d :	5	16	Y3
A 5	d ,	6	15] Y4
A6	d .	7	14	Y5
A7	d :	8	13] Y6
A8	d :	9	12] Y7
GND	þ	10	11] Y8
				-

FUNCTION TABLE

	Inputs	Output Y		
OE1	OE2	Α	Output 1	
LL		ΙΓ	L H	
H X	X H	X X	Z Z	

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 4 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage		- 0.5 to + 7.0	V
V _{in}	DC Input Voltage		- 0.5 to + 7.0	V
V _{out}	DC Output Voltage	DC Output Voltage		V
I _{IK}	Input Diode Current		- 20	mA
I _{OK}	Output Diode Current	Output Diode Current		mA
l _{out}	DC Output Current, per Pin		± 25	mA
I _{CC}	DC Supply Current, V _{CC} and G	IND Pins	± 50	mA
P _D	Power Dissipation in Still Air,	SOIC Package† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature		- 65 to + 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating — SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage		5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	-55	+125	°C
t _r , t _f	Input Rise and Fall Time V_{CC} = 3.3V ± 0.3 V V_{CC} = 5.0V ± 0.5 V	0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			$T_A = 25^{\circ}C$ $T_A = -55 \text{ to}$		to 125°C				
Symbol	Parameter	Test Conditions	v _{cc}	Min	Тур	Max	Min	Max	Unit
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} x 0.7			1.50 V _{CC} x 0.7		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} x 0.3		0.50 V _{CC} x 0.3	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		٧
		$\begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -4\text{mA} \\ I_{OH} &= -8\text{mA} \end{aligned}$	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1	V
		$\begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{OL} &= 4mA \\ I_{OL} &= 8mA \end{aligned}$	3.0 4.5			0.36 0.36		0.44 0.44	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5V or GND	0 to 5.5			± 0.1		± 1.0	μΑ
I _{OZ}	Maximum 3–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH}$ $V_{out} = V_{CC} \text{ or GND}$	5.5			± 0.25		± 2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current	$V_{in} = V_{CC}$ or GND	5.5			4.0		40.0	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

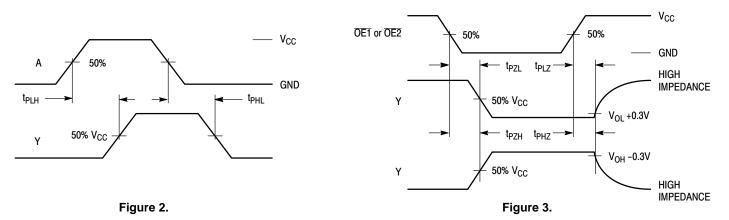
				T _A = 25°C		C $T_A = -55 \text{ to } 125^{\circ}\text{C}$			
Symbol	Parameter	Test Cond	itions	Min	Тур	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		5.0 7.5	7.0 10.5	1.0 1.0	8.5 12.0	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		3.5 5.0	5.0 7.0	1.0 1.0	6.0 8.0	
t _{PZL} , t _{PZH}	Output Enable Time, OE to Y	$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		6.8 9.3	10.5 14.0	1.0 1.0	12.5 16.0	ns
		$V_{CC} = 5.0 \pm 0.5V$ $R_L = 1k\Omega$	$C_L = 15pF$ $C_L = 50pF$		4.7 6.2	7.2 9.2	1.0 1.0	8.5 10.5	
t _{PLZ} , t _{PHZ}	Output Disable Time, OE to Y	$V_{CC} = 3.3 \pm 0.3V$ $R_L = 1k\Omega$	C _L = 50pF		11.2	15.4	1.0	17.5	ns
		$\begin{aligned} V_{CC} &= 5.0 \pm 0.5 V \\ R_L &= 1 k \Omega \end{aligned}$	$C_L = 50pF$		6.0	8.8	1.0	10.0	
t _{OSLH} , t _{OSHL}	Output to Output Skew	V _{CC} = 3.3 ± 0.3V (Note 1)	C _L = 50pF			1.5		1.5	ns
		V _{CC} = 5.0 ± 0.5V (Note 1)	C _L = 50pF			1.0		1.0	ns
C _{in}	Maximum Input Capacitance				4	10		10	pF
C _{out}	Maximum Three–State Output Capacitance (Output in High Impedance State)				6				pF

		Typical @ 25°C, V _{CC} = 5.0V	
C _P	Power Dissipation Capacitance (Note 2)	18	pF

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$, $C_L = 50 \text{pF}$, $V_{CC} = 5.0 \text{V}$)

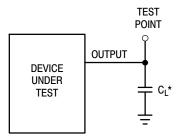
		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.9	1.2	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	- 0.9	- 1.2	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

SWITCHING WAVEFORMS

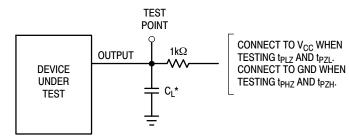


Parameter guaranteed by design. t_{OSLH} = |t_{PLHm} - t_{PLHn}|, t_{OSHL} = |t_{PHLm} - t_{PHLn}|.
 C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

TEST CIRCUITS



*Includes all probe and jig capacitance



*Includes all probe and jig capacitance Figure 5.

Figure 4.

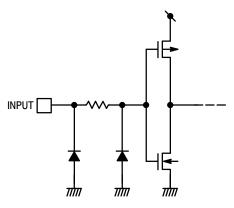


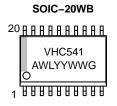
Figure 6. Input Equivalent Circuit

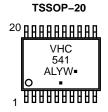
ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC541DWR2G	SOIC-20WB (Pb-Free)	1000 / Tape & Reel
MC74VHC541DTG	TSSOP-20 (Pb-Free)	75 Units / Rail
MC74VHC541DTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MARKING DIAGRAMS





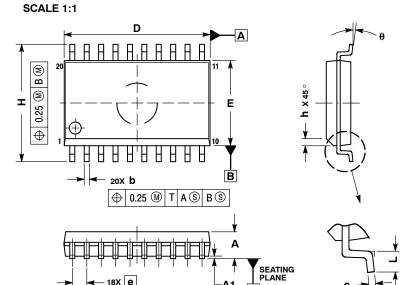
A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or ■ = Pb-Free Package
(Note: Microdot may be in either location)





SOIC-20 WB CASE 751D-05 **ISSUE H**

DATE 22 APR 2015



- DIMENSIONS ARE IN MILLIMETERS.
 INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
b	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
A	0 °	7 °			

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot ΥY = Year WW = Work Week = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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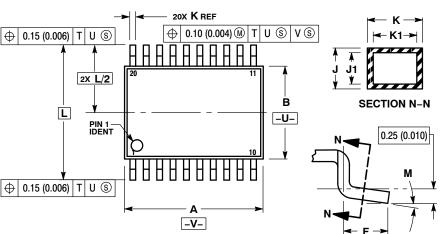
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^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



TSSOP-20 WB CASE 948E ISSUE D

DATE 17 FEB 2016





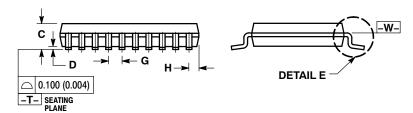
DETAIL E

NOTES:

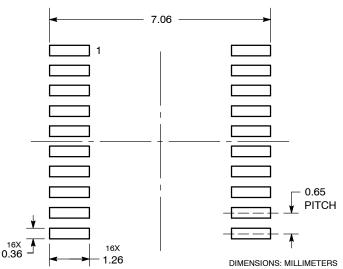
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
- (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 7. DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-

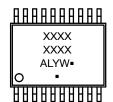
	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°



SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



= Assembly Location

= Wafer Lot = Year

= Work Week

= Pb-Free Package (Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■",

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